

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-16		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\text{ }\mu\text{A}$	-0.4	-0.6	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		2.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -4.5\text{ V}$, $I_D = -8\text{ A}$		20	24	m Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -7\text{ A}$		25	31	
		$V_{GS} = -1.8\text{ V}$, $I_D = -6\text{ A}$		32	45	
		$V_{GS} = -4.5\text{ V}$, $I_D = -8\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		26	36	
g_{FS}	Forward Transconductance	$V_{DD} = -5\text{ V}$, $I_D = -8\text{ A}$		38		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1586	2110	pF
C_{oss}	Output Capacitance			236	355	pF
C_{rss}	Reverse Transfer Capacitance			218	330	pF

Switching Characteristics

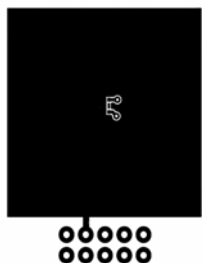
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -8\text{ A}$, $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		9	18	ns
t_r	Rise Time			11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			87	139	ns
t_f	Fall Time			46	74	ns
Q_g	Total Gate Charge	$V_{GS} = -4.5\text{ V}$, $V_{DD} = -10\text{ V}$, $I_D = -8\text{ A}$		15	21	nC
Q_{gs}	Gate to Source Charge			2.2		nC
Q_{gd}	Gate to Drain "Miller" Charge			3.6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -8\text{ A}$ (Note 2)		-0.8	-1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = -1.8\text{ A}$ (Note 2)		-0.7	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		17	31	ns
Q_{rr}	Reverse Recovery Charge			4.1	10	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $60\text{ }^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



b. $175\text{ }^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

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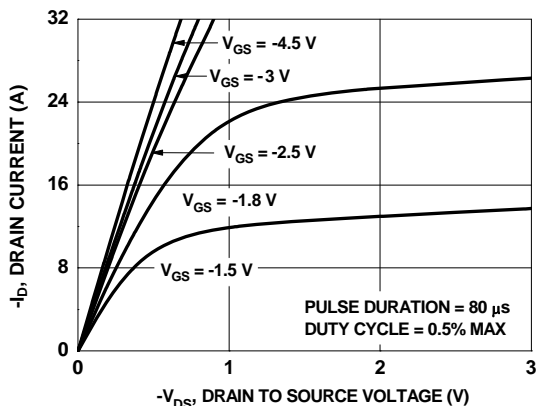


Figure 1. On Region Characteristics

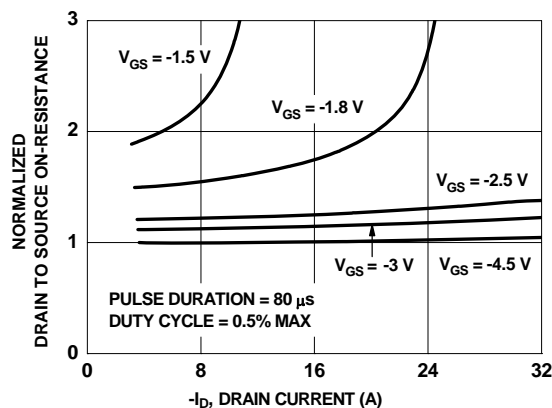


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

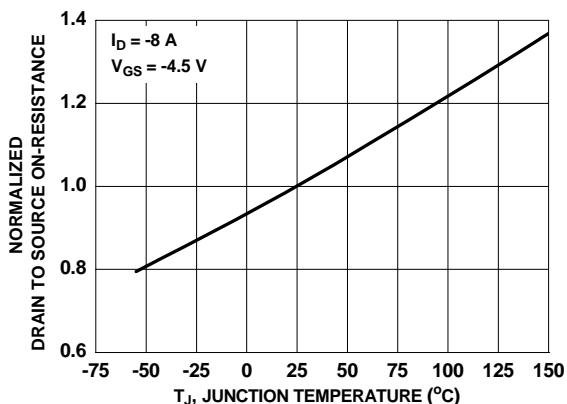


Figure 3. Normalized On Resistance vs Junction Temperature

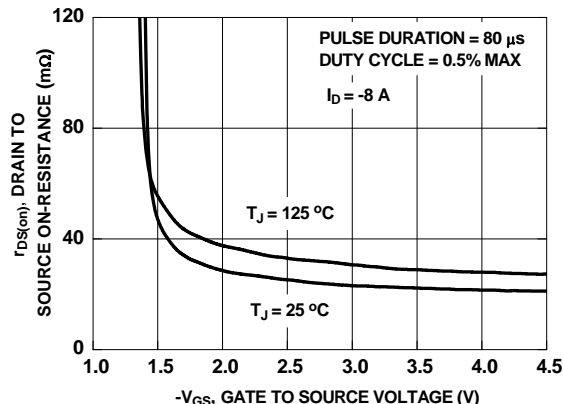


Figure 4. On-Resistance vs Gate to Source Voltage

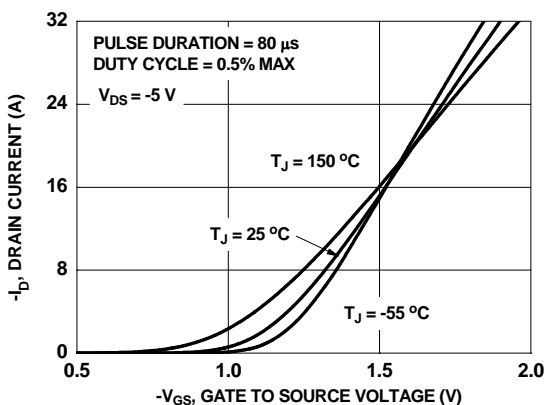


Figure 5. Transfer Characteristics

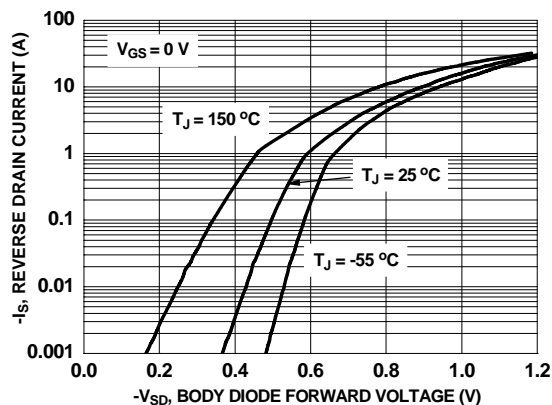


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

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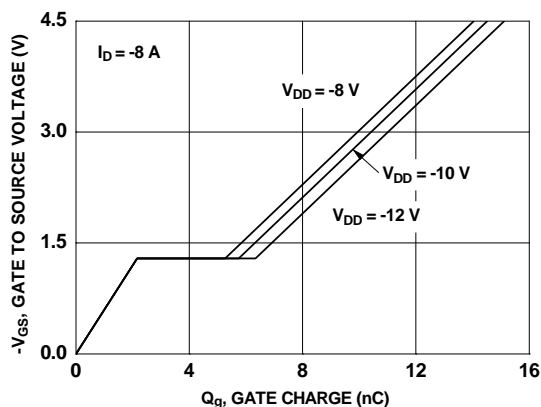


Figure 7. Gate Charge Characteristics

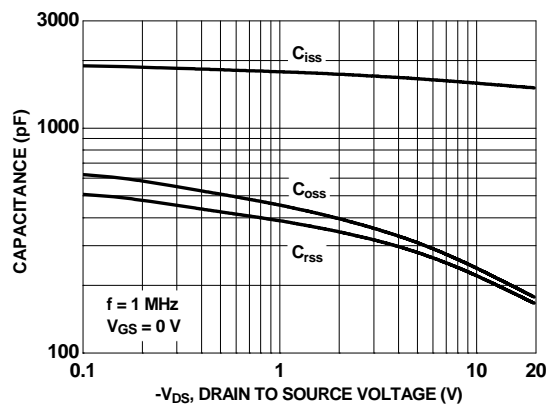


Figure 8. Capacitance vs Drain to Source Voltage

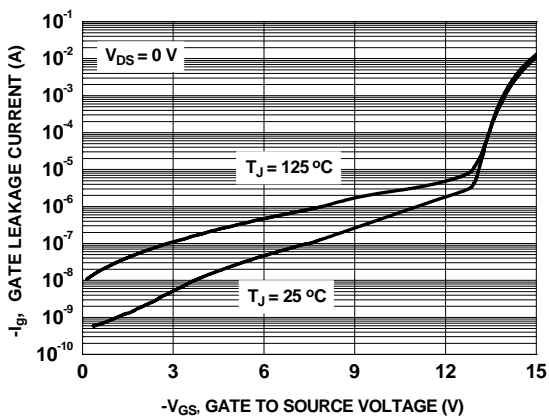


Figure 9. Gate Leakage Current vs Gate to Source Voltage

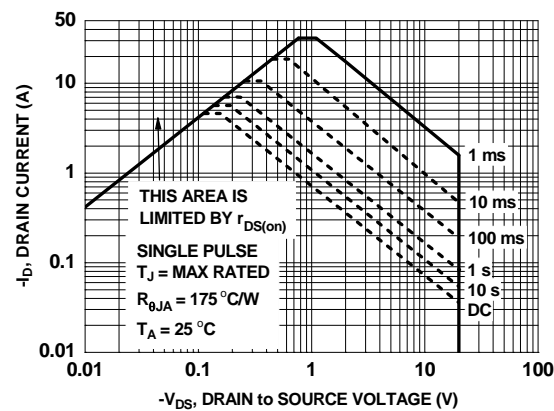


Figure 10. Forward Bias Safe Operating Area

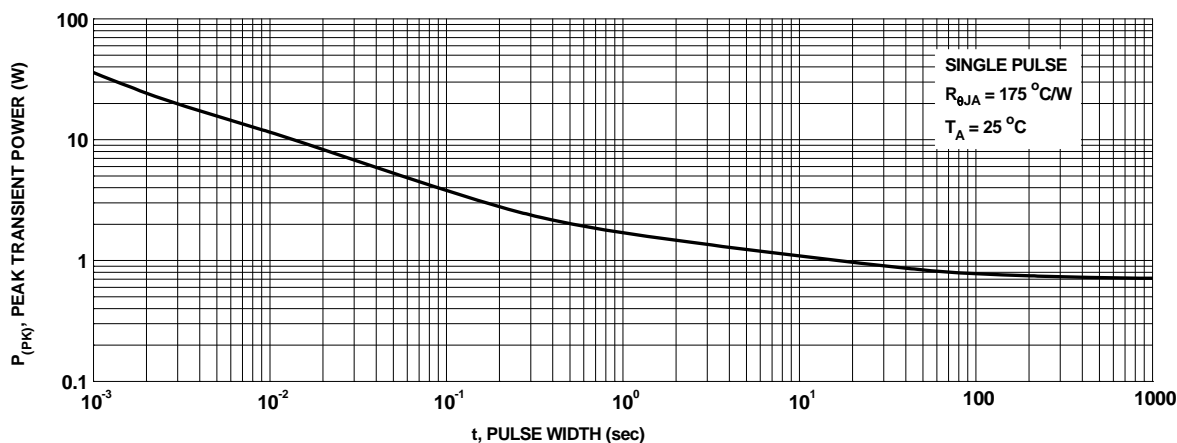


Figure 11. Single Pulse Maximum Power Dissipation

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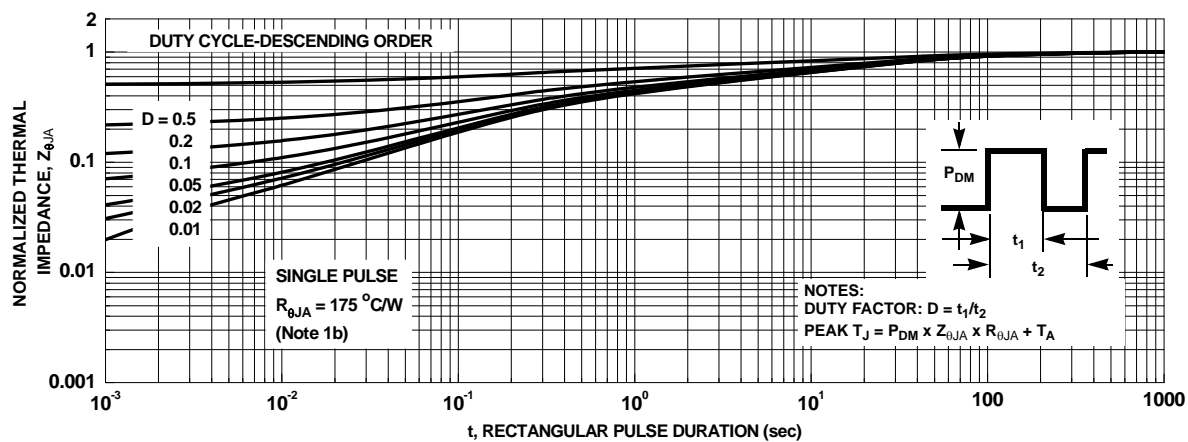
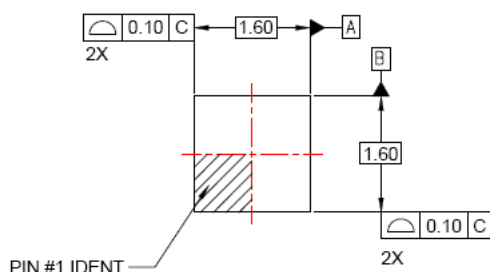
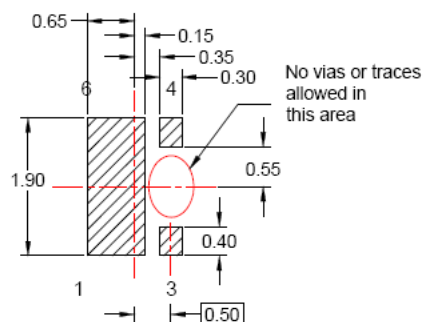


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

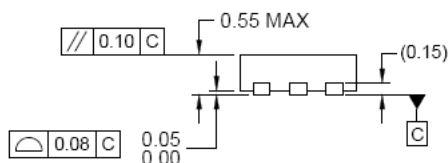
Dimensional Outline and Pad Layout



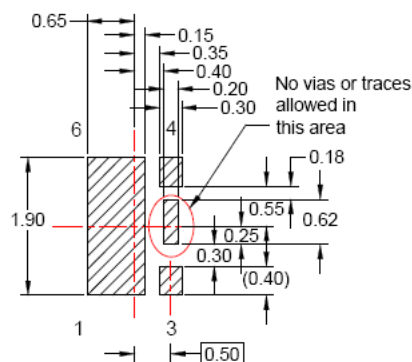
TOP VIEW



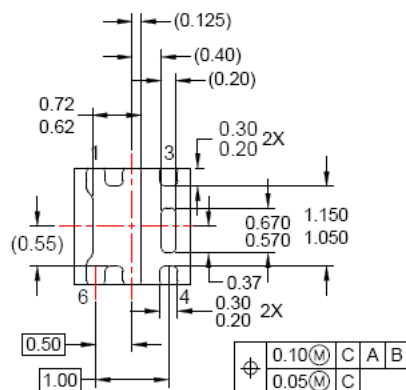
RECOMMENDED LAND PATTERN OPT 1



SIDE VIEW



RECOMMENDED LAND PATTERN OPT 2





NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY

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